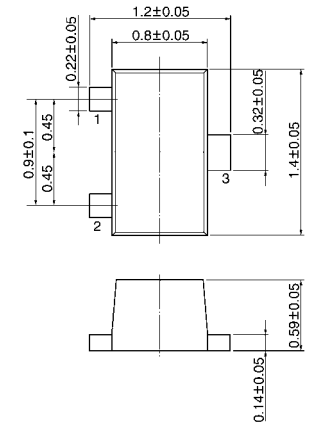
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

RN2107FT, RN2108FT, RN2109FT

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- High-density mount is possible because of devices housed in very thin TESM packages.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Wide range of resistor values are available to use in various circuit designs.
- Complementary to RN1107FT~RN1109FT

Unit: mm



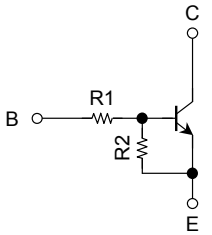
1. BASE
2. EMITTER
3. COLLECTOR

TESM

JEDEC	—
JEITA	—
TOSHIBA	2-1B1A

Weight:0.0022g (typ.)

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2107FT	10	47
RN2108FT	22	47
RN2109FT	47	22

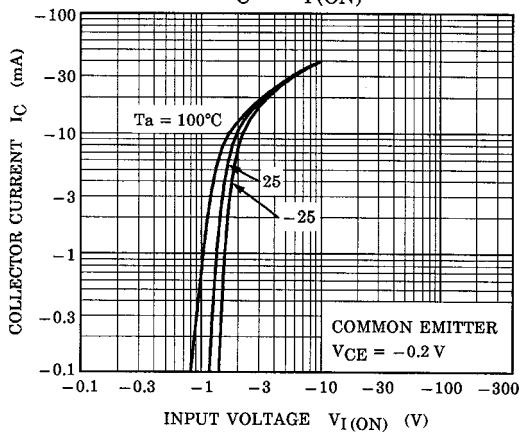
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage	RN2107FT~2109FT	V_{CBO}	−50	V
Collector-emitter voltage		V_{CEO}	−50	V
Emitter-base voltage	RN2107FT	V_{EBO}	−6	V
	RN2108FT		−7	
	RN2109FT		−15	
Collector current	RN2107FT~2109FT	I_C	−100	mA
Collector power dissipation		P_C	100	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55~150	°C

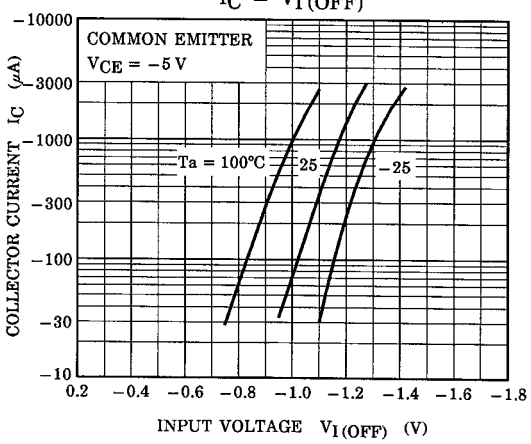
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2107FT~2109FT	I_{CBO}	V_{CB} = −50 V, I_E = 0	—	—	−100	nA
		I_{CEO}	V_{CE} = −50 V, I_B = 0	—	—	−500	
Emitter cut-off current	RN2107FT	I_{EBO}	V_{EB} = −6 V, I_C = 0	−0.081	—	−0.15	mA
	RN2108FT		V_{EB} = −7 V, I_C = 0	−0.078	—	−0.145	
	RN2109FT		V_{EB} = −15 V, I_C = 0	−0.167	—	−0.311	
DC current gain	RN2107FT	h_{FE}	V_{CE} = −5 V, I_C = −10 mA	80	—	—	
	RN2108FT			80	—	—	
	RN2109FT			70	—	—	
Collector-emitter saturation voltage	RN2107FT~2109FT	$V_{CE\ (sat)}$	I_C = −5 mA, I_B = −0.25 mA	—	−0.1	−0.3	V
Input voltage (ON)	RN2107FT	$V_{I\ (ON)}$	V_{CE} = −0.2 V, I_C = −5 mA	−0.7	—	−1.8	V
	RN2108FT			−1.0	—	−2.6	
	RN2109FT			−2.2	—	−5.8	
Input voltage (OFF)	RN2107FT	$V_{I\ (OFF)}$	V_{CE} = −5 V, I_C = −0.1 mA	−0.5	—	−1.0	V
	RN2108FT			−0.6	—	−1.16	
	RN2109FT			−1.5	—	−2.6	
Transition frequency	RN2107FT~2109FT	f_T	V_{CE} = −10 V, I_C = −5 mA	—	250	—	MHz
Collector output capacitance	RN2107FT~2109FT	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	3	6	pF
Input resistor	RN2107FT	R1	—	7	10	13	kΩ
	RN2108FT			15.4	22	28.6	
	RN2109FT			32.9	47	61.1	
Resistor ratio	RN2107FT	R1/R2	—	0.191	0.213	0.232	
	RN2108FT			0.421	0.468	0.515	
	RN2109FT			1.92	2.14	2.35	

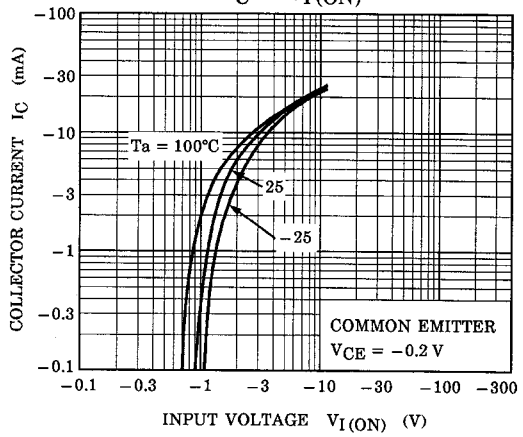
RN2107FT $I_C - V_{I(ON)}$



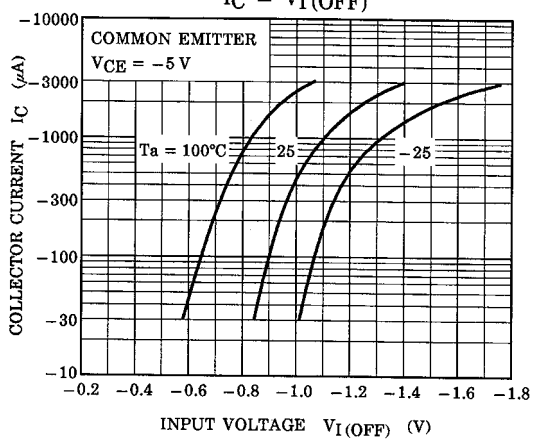
RN2107FT $I_C - V_{I(OFF)}$



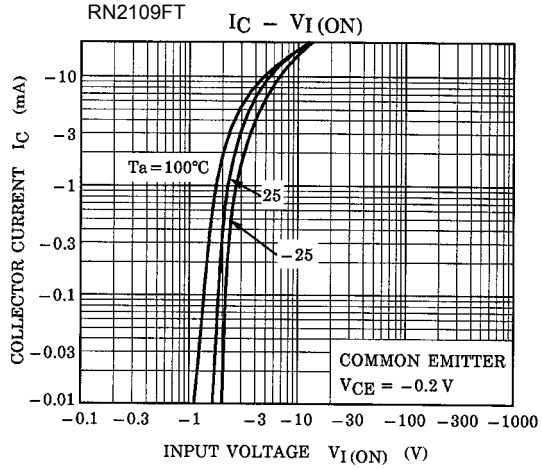
RN2108FT $I_C - V_{I(ON)}$



RN2108FT $I_C - V_{I(OFF)}$



RN2109FT $I_C - V_{I(ON)}$



RN2109FT $I_C - V_{I(OFF)}$